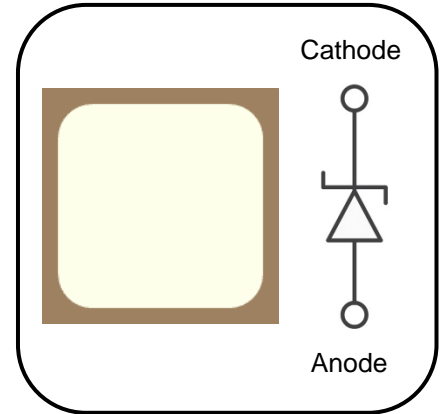


# 4<sup>th</sup> Generation 650V/4A SiC Schottky Barrier Diode

## Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant



## Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies



## Description

The SDS065J004B4 SiC Schottky Barrier Diode (SBD) has been developed using Sanan’s advanced 4<sup>th</sup> generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 650V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

## Product Specifications

Device	$V_{RRM}$	$I_F (135^\circ C)$	$V_F (25^\circ C)$	$Q_C$
SDS065J004B4	650V	7A	1.27V	11nC

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**Table 1. Maximum Ratings**

(T<sub>c</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V <sub>RRM</sub>	650	V	T <sub>C</sub> = 25°C
Surge peak reverse voltage	V <sub>RSM</sub>	650		T <sub>C</sub> = 25°C
DC reverse voltage	V <sub>DC</sub>	650		T <sub>C</sub> = 25°C
Continuous forward current	I <sub>F</sub>	15	A	T <sub>C</sub> = 25°C
		7		T <sub>C</sub> = 135°C
		4		T <sub>C</sub> = 155°C
Surge non-repetitive forward current	I <sub>FSM</sub>	32	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine pulse
Repetitive peak forward current	I <sub>FRM</sub>	25	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine wave D = 0.1
i <sup>2</sup> t value	∫i <sup>2</sup> dt	5.1	A <sup>2</sup> s	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms
Operating junction temperature	T <sub>j</sub>	-55~175	°C	
Storage temperature	T <sub>stg</sub>	-55~175	°C	

**Table 2. Thermal Resistance**

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R <sub>th(j-c)</sub>	/	2.15	/	°C/W	

\*Thermal Resistance is collected in TO-220-2L

**Table 3. Static Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V <sub>DC</sub>	650	/	/	V	I <sub>R</sub> = 100 μA
Forward voltage	V <sub>F</sub>	/	1.27	1.45	V	I <sub>F</sub> = 4A, T <sub>j</sub> = 25°C
		/	1.45	1.70		I <sub>F</sub> = 4A, T <sub>j</sub> = 175°C
Reverse current	I <sub>R</sub>	/	3	24	μA	V <sub>R</sub> = 650V, T <sub>j</sub> = 25°C
		/	10	96		V <sub>R</sub> = 650V, T <sub>j</sub> = 175°C

**Table 4. Dynamic Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	231	/	pF	V <sub>R</sub> = 0V, f = 1MHz
		/	21	/		V <sub>R</sub> = 200V, f = 1MHz
		/	17	/		V <sub>R</sub> = 400V, f = 1MHz
Total capacitive charge	Q <sub>C</sub>	/	11	/	nC	V <sub>R</sub> = 400V
Capacitance stored energy	E <sub>C</sub>	/	1.6	/	μJ	V <sub>R</sub> = 400V

### Electrical Characteristic Diagrams

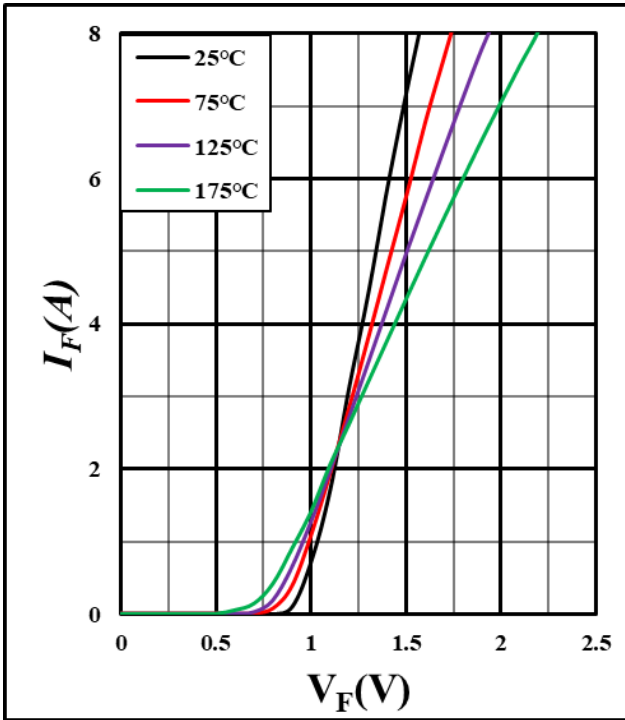


Figure 1. Forward characteristics

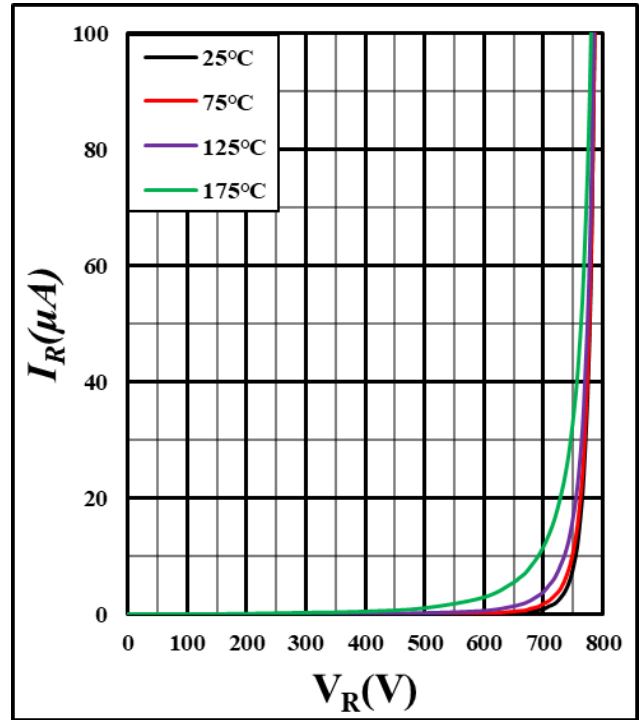


Figure 2. Reverse characteristics

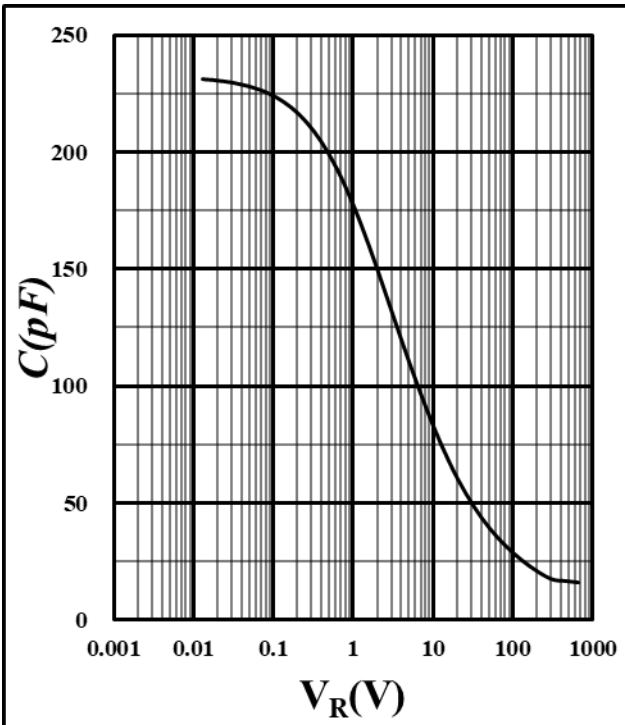


Figure 3. Capacitance vs. reverse voltage

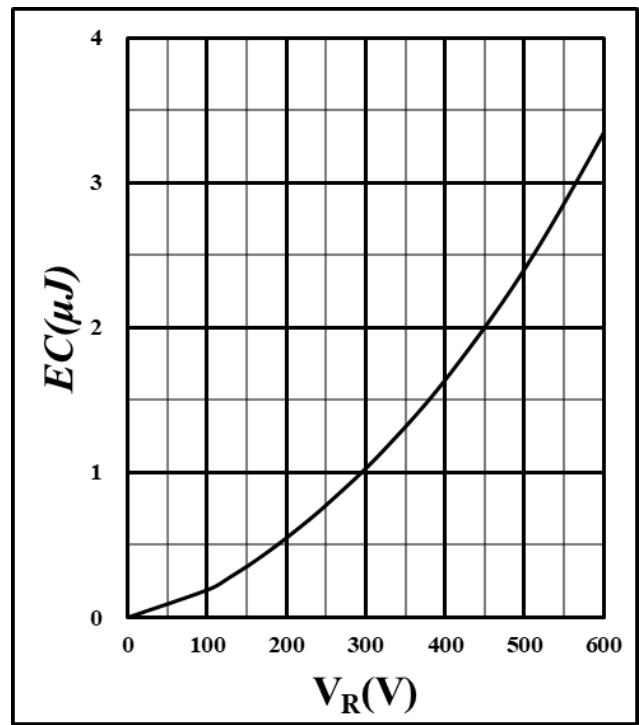


Figure 4. Capacitance stored energy

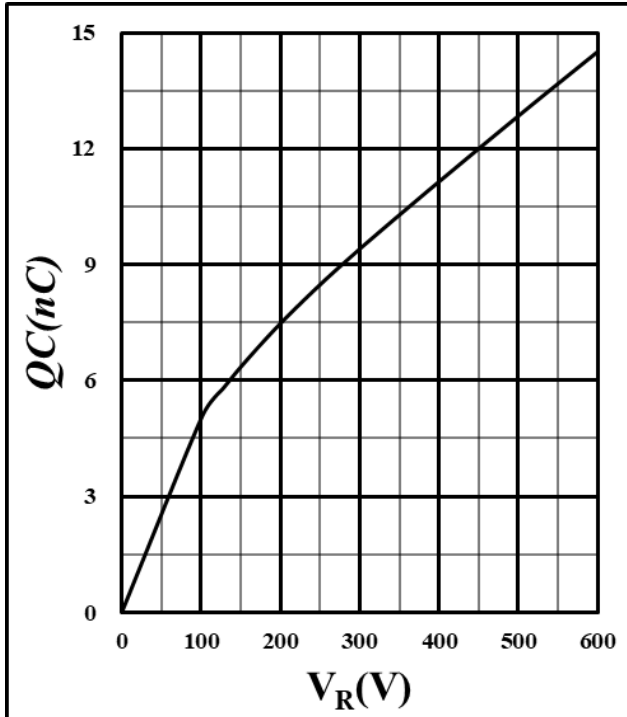


Figure 5. Total capacitance charge vs. reverse voltage

## Ordering Information

Part Number	SDS065J004B4
Package	Bare Die
Packing Method	Wafer
RoHS	Yes

## Important Notices – Read Carefully

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